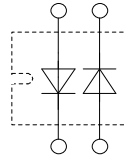


# HiPerFRED

High Performance Fast Recovery Diode  
 Low Loss and Soft Recovery  
 Anti-parallel legs

Part number

**DSEP2x60-12A**



Backside: isolated

E72873

**Features / Advantages:**

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I<sub>rm</sub>-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I<sub>rm</sub> reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

**Applications:**

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

**Package:**

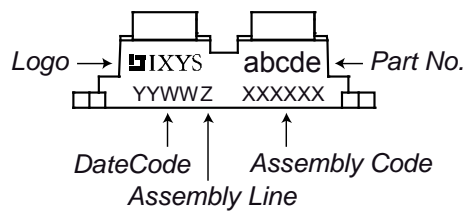
- Housing: SOT-227B (minibloc)
- Industry standard outline
- Cu base plate internal DCB isolated
- Isolation Voltage 3000 V
- Epoxy meets UL 94V-0
- RoHS compliant

**Ratings**

Symbol	Definition	Conditions	Ratings			Unit
			min.	typ.	max.	
V <sub>RRM</sub>	max. repetitive reverse voltage	T <sub>VJ</sub> = 25 °C			1200	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 1200 V			1	mA
		V <sub>R</sub> = 1200 V			4	mA
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 60 A	T <sub>VJ</sub> = 25 °C		2.42	V
					2.84	V
		I <sub>F</sub> = 120 A	T <sub>VJ</sub> = 150 °C		1.52	V
					1.92	V
I <sub>FAV</sub>	average forward current	rectangular d = 0.5	T <sub>C</sub> = 80 °C		60	A
V <sub>F0</sub>	threshold voltage	} for power loss calculation only	T <sub>VJ</sub> = 150 °C		1.15	V
r <sub>F</sub>	slope resistance				6.2	mΩ
R <sub>thJC</sub>	thermal resistance junction to case				0.60	K/W
T <sub>VJ</sub>	virtual junction temperature		-40		150	°C
P <sub>tot</sub>	total power dissipation		T <sub>C</sub> = 25 °C		200	W
I <sub>FSM</sub>	max. forward surge current	t = 10 ms (50 Hz), sine	T <sub>VJ</sub> = 45 °C		800	A
I <sub>RM</sub>	max. reverse recovery current		T <sub>VJ</sub> = 25 °C		8	A
		I <sub>F</sub> = 60 A; V <sub>R</sub> = 800 V	T <sub>VJ</sub> = 125 °C		60	A
t <sub>rr</sub>	reverse recovery time	-di <sub>F</sub> /dt = 600 A/μs	T <sub>VJ</sub> = 25 °C		60	ns
			T <sub>VJ</sub> = 125 °C		220	ns
C <sub>J</sub>	junction capacitance	V <sub>R</sub> = 600 V; f = 1 MHz	T <sub>VJ</sub> = 25 °C		48	pF

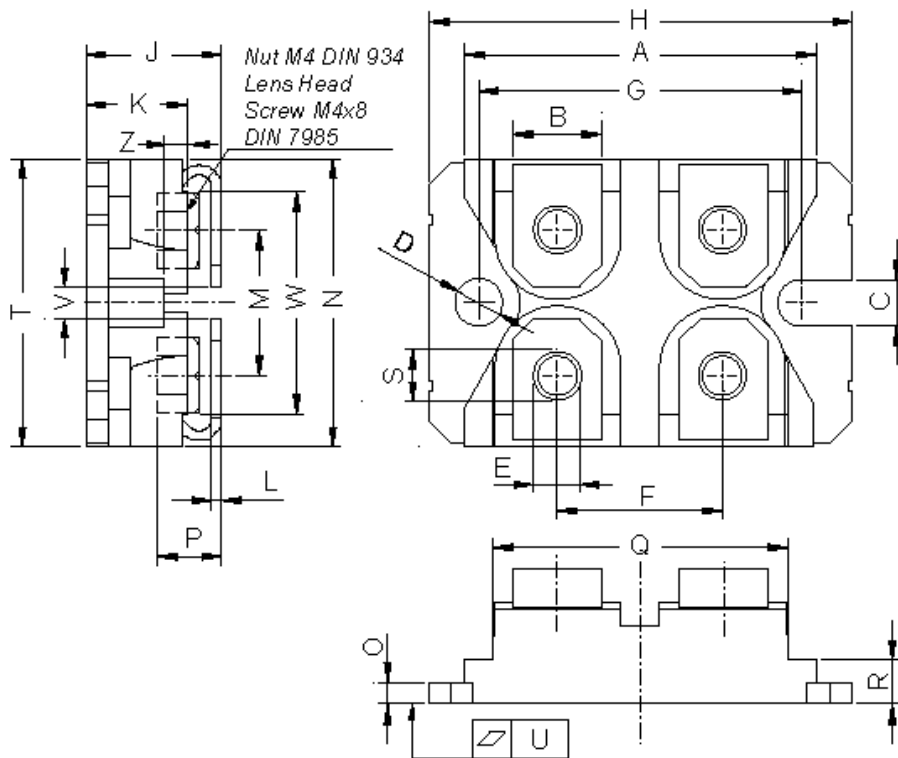
Symbol	Definition	Conditions	Ratings			Unit
			min.	typ.	max.	
$I_{RMS}$	RMS current	per terminal			100	A
$R_{thCH}$	thermal resistance case to heatsink			0.10		K/W
$T_{stg}$	storage temperature		-40		150	°C
<b>Weight</b>				30		g
$M_D$	mounting torque		1.1		1.5	Nm
$M_T$	terminal torque		1.1		1.5	Nm
$V_{ISOL}$	isolation voltage	t = 1 second	3000			V
		t = 1 minute	2500			V
$d_{Spp/App}$	creepage   striking distance on surface   through air	terminal to terminal	10.5	3.2		mm
$d_{Spb/Apb}$	creepage   striking distance on surface   through air	terminal to backside	8.6	6.8		mm

### Product Marking



Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Code Key
Standard	DSEP2x60-12A	DSEP2x60-12A	Tube	10	495840

Similar Part	Package	Voltage Class
DSEP2x61-12A	SOT-227B (minibloc)	1200

**Outlines SOT-227B (minibloc)**


Dim.	Millimeter		Inches	
	min	max	min	max
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.23	1.488	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.74	0.84	0.029	0.033
M	12.50	13.10	0.492	0.516
N	25.15	25.42	0.990	1.001
O	1.95	2.13	0.077	0.084
P	4.95	6.20	0.195	0.244
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.167
S	4.55	4.85	0.179	0.191
T	24.59	25.25	0.968	0.994
U	-0.05	0.10	-0.002	0.004
V	3.20	5.50	0.126	0.217
W	19.81	21.08	0.780	0.830
Z	2.50	2.70	0.098	0.106

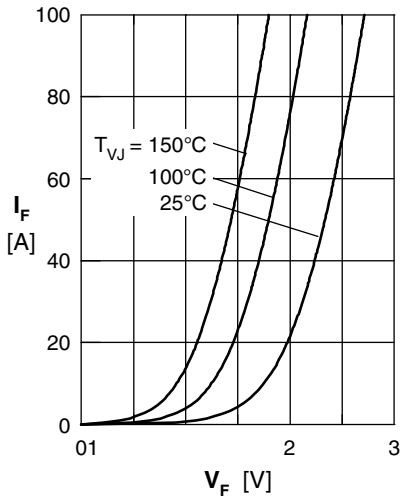


Fig. 1 Forward current  $I_F$  vs.  $V_F$

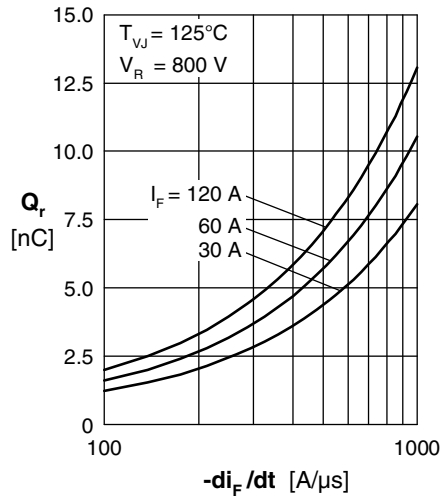


Fig. 2 Reverse recovery charge  $Q_r$  versus  $-di_F/dt$

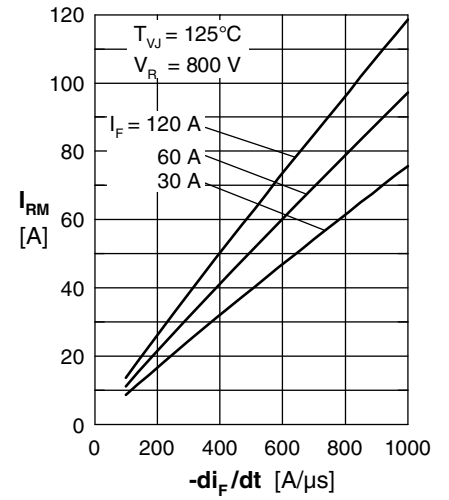


Fig. 3 Peak reverse current  $I_{RM}$  versus  $-di_F/dt$

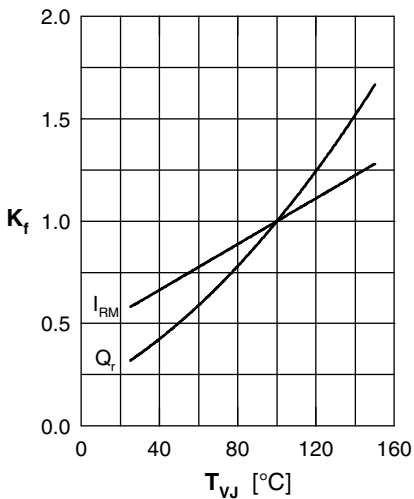


Fig. 4 Dynamic parameters  $Q_r$ ,  $I_{RM}$  versus  $T_{VJ}$

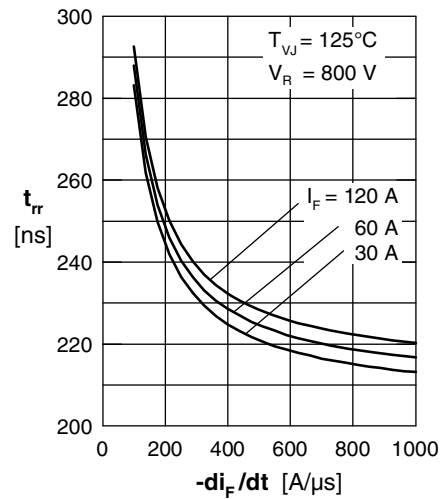


Fig. 5 Recovery time  $t_{tr}$  versus  $-di_F/dt$

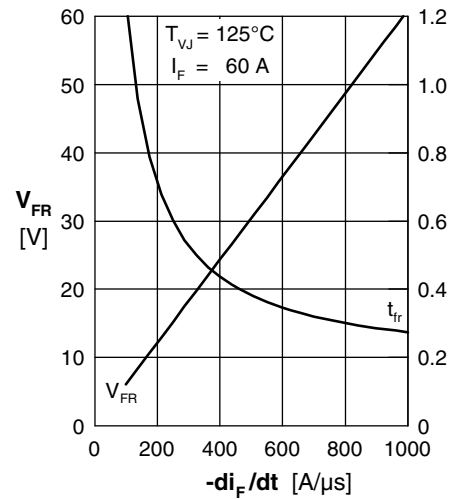


Fig. 6 Peak forward voltage  $V_{FR}$  and  $t_{tr}$  versus  $di_F/dt$

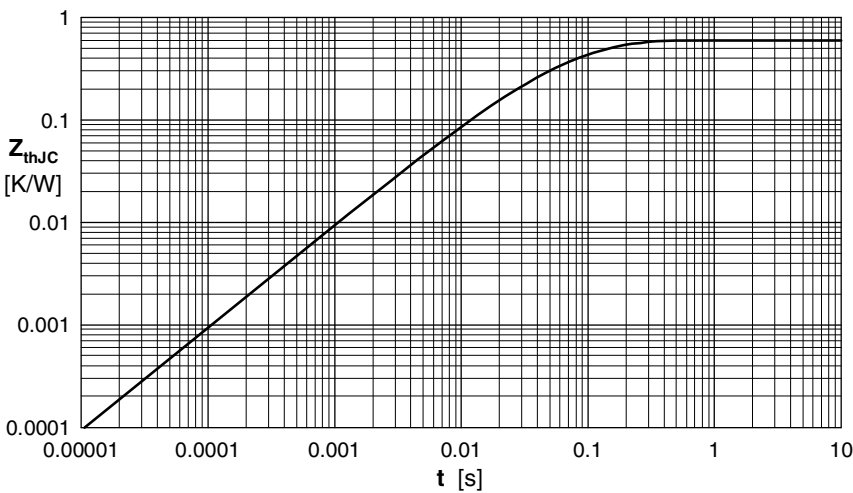


Fig. 7 Transient thermal resistance junction to case

Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.212	0.0055
2	0.248	0.0092
3	0.063	0.0007
4	0.077	0.0391